- 2.7-V and 5-V Performance
- No Crossover Distortion
- Low Supply Current at V_{CC+} = 5 V:

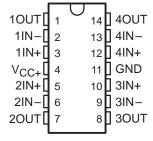
TLV821 ... 0.3 mA Typ TLV822 ... 0.5 mA Typ TLV824 ... 1 mA Typ

- Rail-to-Rail Output Swing
- Pin-to-Pin Compatible with LMV821, LMV822, and LMV824 Devices
- Package Options Include Plastic Small-Outline (D), Small-Outline Transistor (SOT-23 DBV, SC-70 DCK), and Thin Shrink Small-Outline (PW) Packages

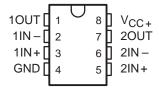
description

The TLV821, TLV822, and TLV824 devices are low-voltage (2.5 V to 5.5 V) low-power operational amplifiers, designed to be functionally and pin-to-pin compatible with the LMV821, LMV822, and LMV824 devices. Electrical characteristics are very similar to the LMV3xx operational amplifiers (low supply current, rail-to-rail outputs, input common-mode range, which includes ground). The TLV8xx devices have a significantly higher bandwidth (8 MHz typically) and a 2.5-V/µs slew rate. The TLV821 is a single, the TLV822 is a dual, and the TLV824 is a quad operational amplifier.

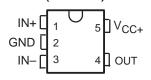
TLV824 . . . D OR PW PACKAGE (TOP VIEW)



TLV822...D OR PW PACKAGE (TOP VIEW)



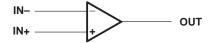
TLV821 ... DBV OR DCK PACKAGE (TOP VIEW)



These devices are the most cost-effective solution for applications requiring low-voltage/low-power operation and space-saving considerations. The TLV821 is available in the ultra-small DCK package, which is approximately half the size of the DBV package. The DCK package saves space on PC boards and enables the design of small portable electronic devices (cordless and cellular phones, laptops, PDAs, PCMIAs). It also allows the designer to place the device closer to the signal source to reduce noise pickup and increase signal integrity.

The TLV821I, TLV822I, and TLV824I devices are characterized for operation from −40°C to 85°C.

symbol (each amplifier)



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AVAILABLE OPTIONS

т.	PACKAGE	PACKAGED DEVICES					
TA	TYPE	SINGLE	DUAL	QUADRUPLE			
–40°C to 85°C	E nin COT	TLV821IDCKR	_	_			
	5-pin SOT	TLV821IDBVR	_	_			
	8-pin SOIC	_	TLV822ID	_			
	8-pin TSSOP	— TLV822IPWR		_			
	14-pin SOIC	_	_	TLV824ID			
	14-pin TSSOP	_	_	TLV824IPWR			

The D package is available taped and reeled. Add the suffix R to the device type (e.g., TLV824IDR). The DCK, DBV, and PW packages are only available left-end taped and reeled.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{CC} (see Note 1)		5.5 V
Differential input voltage, V _{ID} (see Note 2)		±5.5 V
Input voltage range, V _I (either input)		
Duration of output short circuit (one amplifier) to ground		
V _{CC} ≤ 5.5 V (see Note 3)		Unlimited
Operating virtual junction temperature		
Package thermal impedance, θ_{JA} (see Notes 4 and 5):	D (8-pin) package	97°C/W
	D (14-pin) package	86°C/W
	DBV package	347°C/W
	DCK package	389°C/W
	PW (8-pin) package	149°C/W
	PW (14-pin) package	113°C/W
Lead temperature 1,6 mm (1/16 inch) from case for 10	seconds: D or PW package	260°C
Storage temperature range, T _{sto}		65 to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values (except differential voltages and VCC specified for the measurement of IOS) are with respect to the network GND.

- 2. Differential voltages are at IN+ with respect to IN-.
- 3. Short circuits from outputs to $V_{\hbox{\footnotesize{CC}}}$ can cause excessive heating and eventual destruction.
- Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is P_D = (T_J(max) T_A)/θ_{JA}. Selecting the maximum of 150°C can affect reliability.
- 5. The package thermal impedance is calculated in accordance with JESD 51.



PRODUCT PREVIEW

recommended operating conditions

		MIN	MAX	UNIT
VCC	Supply voltage (single-supply operation)	2.5	5.5	V
TA	Operating free-air temperature	-40	85	°C

electrical characteristics at specified free-air temperature, V_{CC+} = 2.7 V, GND= 0 V, V_{CM} = 1 V, V_O = 1.35 V, and R_L > 1 M Ω (unless otherwise noted)

	PARAMETER	TEST CONDITION	ONS	TA	MIN	TYP	MAX	UNIT
1/1-	lanut offeet valtage			25°C		1	3.5	\/
VIO	Input offset voltage			-40°C to 85°C			4	mV
$\alpha_{V_{IO}}$	Average temperature coefficient of input offset voltage			25°C		1		μV/°C
I _{IB}	I _{IB} Input bias current			25°C		30	90	nA
IIB	input bias current			–40°C to 85°C			140	ПА
lio.	I _{IO} Input offset current			25°C		0.5	30	nA
10	mpat onset ourrent			–40°C to 85°C			50	117 (
CMRR	Common-mode rejection ratio	V _{CM} = 0 to 1.7 V		25°C	60	73		dB
OWITAT	- Common mode rejection ratio	VCIVI = 0 to 1.7 V		–40°C to 85°C	58			ub_
	Positive supply-voltage	$V_{CC+} = 1.7 \text{ V to 4 V},$		25°C	60	75		-10
+ksvr	rejection ratio	GND = 1 V, V _{CM} = 0, V _O = 0		–40°C to 85°C	58			dB
	Negative supply-voltage	V _{CC+} = 1.7 V,		25°C	60	75		dB
-ksvr	rejection ratio	QND = -1 V to -3.3 V, QCM = 0, VO = 0	GND = -1 V to -3.3 V, V _{CM} = 0, V _O = 0		58			
\/.o.	Common-mode input voltage	OMPD > 50 JP		25°C	-0.2	-0.3		V
VICR	range	CMRR ≥ 50 dB 25	25°C	1.9	2			
		$R_L = 600 \Omega \text{ to } 1.35 \text{ V},$ $V_O = 1.35 \text{ V to } 2.2 \text{ V}$	Sourcing	25°C	90	100		dB
			Courcing	–40°C to 85°C	85			
	Large-signal differential-voltage amplification	$R_L = 600 \Omega$ to 1.35 V, $V_O = 1.35 V$ to 0.5 V	Sinking	25°C	85	90		
A _{VD}				–40°C to 85°C	80			
		$R_L = 2 \text{ k}\Omega \text{ to } 1.35 \text{ V},$ $V_O = 1.35 \text{ V to } 2.2 \text{ V}$	Sourcing	25°C	95	100		
				–40°C to 85°C	90			
		$R_L = 2 \text{ k}\Omega \text{ to } 1.35 \text{ V},$ VO = 1.35 V to 0.5 V	Sinking	25°C	90	95		
			Olliking	–40°C to 85°C	85			
			High level	25°C	2.5	2.58		V
		$V_{CC+} = 2.7 \text{ V},$	riigirievei	–40°C to 85°C	2.4			
	Output swing	R_L = 600 Ω to 1.35 V	Low level	25°C		0.13	0.2	
			LOW IOVOI	–40°C to 85°C			0.3	
			High level	25°C	2.6	2.66		
		$V_{CC+} = 2.7 \text{ V},$ $R_L = 2 \text{ k}\Omega \text{ to } 1.35 \text{ V}$	riigirievei	–40°C to 85°C	2.5			
			Low level	25°C		0.08	0.12	
		Low level		–40°C to 85°C			0.2	

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electrical characteristics at specified free-air temperature, V_{CC+} = 2.7 V, GND = 0 V, V_{CM} = 1 V, V_O = 1.35 V, and R_L > 1 M Ω (unless otherwise noted) (continued)

PARAMETER		TEST CONDITIONS		TA	MIN	TYP	MAX	UNIT
	Output current	VO = 0 V	Sourcing	25°C	12	16		A
10		V _O = 2.7 V	Sinking	25°C	12	26		mA
		TLV821I		25°C		0.22	0.3	
		TLVOZII		–40°C to 85°C			0.5	
laa	Cumply ourrent	TI / (2001 //)		25°C		0.45	0.6	
ICC	Supply current	TLV822I (both amplifiers)		-40°C to 85°C			0.8	mA
		TLV824I (all four amplifiers)		25°C		0.72	1	
				-40°C to 85°C			1.2	
SR	Slew rate	V _{CC+} = 5 V [†]		25°C		2		V/μs
GBM	Gain-bandwidth product			25°C		7		MHz
φm	Phase margin			25°C		61		deg
Gm	Gain margin			25°C		10		dB
	Amplifier-to-amplifier isolation	$V_{CC+} = 5 \text{ V}, R_L = 100 \text{ k}\Omega$	$V_{CC+} = 5 \text{ V}, R_L = 100 \text{ k}\Omega \text{ to } 2.5 \text{ V}^{\ddagger}$			135		dB
Vn	Equivalent input noise voltage	f = 1 kHz, V _{CM} = 1 V		25°C		28		nV/√ Hz
In	Equivalent input noise voltage	f = 1 kHz		25°C		0.1		pA/√ Hz
THD	Total harmonic distortion	f = 1 kHz, $A_{VD} = -2$, $R_L = 10 \text{ k}\Omega$, V_C) = 4.1 Vpp	25°C		0.01%		

[†] Connected as voltage follower with 3-V step input. Value specified is the slower of the positive and negative slew rates.



[‡] Refers to inputs only. Each amplifier is excited, in turn, with 1 kHz to produce $V_0 = 3 \text{ Vpp.}$

PRODUCT PREVIEW

electrical characteristics at specified free-air temperature, V_{CC+} = 5 V, GND= 0 V, V_{CM} = 2 V, V_O = 2.5 V, and R_L > 1 M Ω (unless otherwise noted)

	PARAMETER	TEST CONDITI	ONS	TA	MIN	TYP	MAX	UNIT
\/	lanut offeet veltege			25°C		1	3.5	\/
VIO	Input offset voltage			–40°C to 85°C			4	mV
$\alpha_{V_{IO}}$	Average temperature coefficient of input offset voltage			25°C		1		μV/°C
l.s	Input bias current			25°C		40	100	nA
IB	input bias current			-40°C to 85°C			150	IIA
1.0	Input offset current			25°C		0.5	30	nA
liO	input onset current			-40°C to 85°C			50	ПА
CMRR	Common-mode rejection	V _{CM} = 0 to 4 V		25°C	62	75		dB
Civilata	ratio	VCW = 0 10 4 V		–40°C to 85°C	60			uВ
	Positive supply-voltage	$V_{CC+} = 1.7 \text{ V to 4 V},$		25°C	60	75		
+kSVR	rejection ratio	GND = -1 V, $V_{CM} = 0, V_{O} = 0$		–40°C to 85°C	58			dB
1.	Negative supply-voltage	V _{CC+} = 1.7 V,		25°C	60	75		JD.
-ksvr	rejection ratio	GND = -1 V to -3.3 V, V _{CM} = 0, V _O = 0		–40°C to 85°C	58			dB
VICR	Common-mode input	CMRR ≥ 50 dB	CMRR > 50 dB		-0.2	-0.3		V
·ICK	voltage range	S 1 2 3 4 2		25°C	4.2	4.3		
	Large-signal differential-voltage	$R_L = 600 \Omega \text{ to } 2.5 \text{ V},$ $V_O = 2.5 \text{ V to } 4.5 \text{ V}$	Sourcing	25°C	95	105		dB
			Joanna	–40°C to 85°C	90			
		$\begin{aligned} R_L &= 600 \ \Omega \ \ \text{to} \ 2.5 \ \text{V}, \\ V_O &= 2.5 \ \text{V} \ \text{to} \ 0.5 \ \text{V} \end{aligned} \qquad \text{Sinking} \\ R_L &= 2 \ \text{k} \Omega \ \text{to} \ 2.5 \ \text{V}, \\ V_O &= 2.5 \ \text{V} \ \text{to} \ 4.5 \ \text{V} \end{aligned} \qquad \text{Sourcir} \\ R_L &= 2 \ \text{k} \Omega \ \text{to} \ 2.5 \ \text{V}, \\ V_O &= 2.5 \ \text{V} \ \text{to} \ 0.5 \ \text{V} \end{aligned} \qquad \text{Sinking} $	Sinking	25°C	95	105		
AVD				–40°C to 85°C	90			
7.00	amplification		Sourcing	25°C	95	105		
				–40°C to 85°C	90			
				25°C	95	105		
			Olinking	–40°C to 85°C	90			
			High level	25°C	4.75	4.84		
		$V_{CC+} = 5 \text{ V},$	riigirievei	–40°C to 85°C	4.7			
		$R_L = 600 \Omega \text{ to } 2.5 \text{ V}$	Low level	25°C		0.17	0.25	
	Output owing		Low level	–40°C to 85°C			0.3	
	Output swing		High lovel	25°C	4.85	4.9		V
	$V_{CC+} = 5 V$,	High level	–40°C to 85°C	4.8			1	
	$R_1 = 2 k\Omega$ to 2.5 V	1	25°C		0.1	0.15		
			Low level	–40°C to 85°C			0.2	1
		\/- 0\/	Coversion	25°C	20	45		mA
1-	Output ourse	V _O = 0 V	Sourcing	–40°C to 85°C	15			
Ю	Output current	V 5V	Cialsia a	25°C	20	40		
		V _O = 5 V Sinking		–40°C to 85°C	15			

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electrical characteristics at specified free-air temperature, V_{CC+} = 5 V, GND = 0 V, V_{CM} = 2 V, V_O = 2.5 V, and R_L > 1 M Ω (unless otherwise noted) (continued)

	PARAMETER	TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
		TI \ (004)	25°C		0.3	0.4	
		TLV821I	–40°C to 85°C			0.6	
100	Supply current	TLV822I (both amplifiers)	25°C		0.5	0.7	mΛ
¹ CC	Supply current	TEVOZZI (botti ampliliers)	–40°C to 85°C			0.9	mA
		TLV824I (all four amplifiers)	25°C		1	1.3	
			–40°C to 85°C			1.5	
SR	Slew rate	V _{CC+} = 5 V [†]	25°C	2	2.5		V/μs
GBM	Gain-bandwidth product		25°C		8		MHz
φm	Phase margin		25°C		67		deg
Gm	Gain margin		25°C		15		dB
	Amplifier-to-amplifier isolation	$V_{CC+} = 5 \text{ V}, R_L = 100 \text{ k}\Omega \text{ to } 2.5 \text{ V}^{\ddagger}$	25°C		135		dB
Vn	Equivalent input noise voltage	f = 1 kHz, V _{CM} = 1 V	25°C		24		nV/√ Hz
In	Equivalent input noise voltage	f = 1 kHz	25°C		0.25		pA/√ Hz
THD	Total harmonic distortion	f = 1 kHz, $A_{VD} = -2$, $R_L = 10 \text{ k}Ω$, $V_O = 4.1 \text{ Vpp}$	25°C		0.01%	·	

[†] Connected as voltage follower with 3-V step input. Value specified is the slower of the positive and negative slew rates.



[‡] Refers to inputs only. Each amplifier is excited, in turn, with 1 kHz to produce $V_0 = 3 V_{PP}$.

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